

UNISONIC TECHNOLOGIES CO., LTD

UT3N06 Preliminary Power MOSFET

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

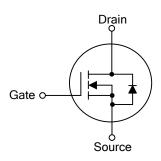
DESCRIPTION

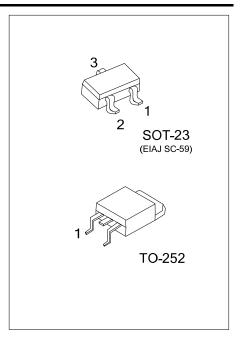
The UTC UT3N06 is an N-channel power MOSFET providing very low on-resistance. It has high efficiency and perfect cost-effectiveness. It can be generally applied in the commercial and industrial fields.

FEATURES

* Simple drive requirement

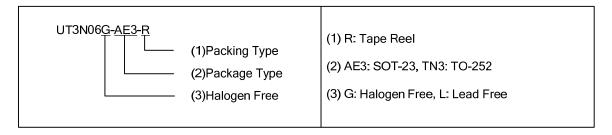
SYMBOL



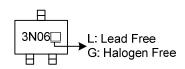


ORDERING INFORMATION

Ordering Number		Doolsons	Pin Assignment			Doolsing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT3N06L-AE3-R	UT3N06G-AE3-R	SOT-23	S	G	D	Tape Reel	
UT3N06L-TN3-R	UT3N06G-TN3-R	TO-252	G	D	S	Tape Reel	
UT3N06L-TN3-T	UT3N06G-TN3-T	TO-252	G	D	S	Tube	



MARKING



ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (V _{GS} =4.5V, T _A = 25°C) (Note 2)		I _D	3.0	А
Pulsed Drain Current (Note 3, 4)		I _{DM}	10	Α
Power Dissipation (T _A = 25°C)	SOT-23		0.35	W
	TO-252	P_{D}	1.13	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

- Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 - 2. Surface mounted on 1 in² copper pad of FR4 board; 270°C/W when mounted on min. copper pad.
 - 3. Pulse width limited by $T_{J(MAX)}$
 - 4. Pulse width ≤300µs, duty cycle≤2%.

THERMAL DATA

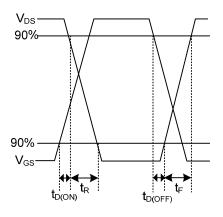
PARAMETER		SYMBOL	RATING	UNIT	
	SOT-23	θυΑ	350	°C/W	
Junction to Ambient	TO-252		110	°C/W	

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

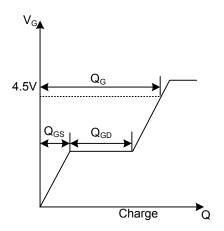
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250 \mu A$	60			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Reference to 25°C, I _D =1mA		0.05		V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			10	μΑ
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.0		3.0	V
Duit to Out of the Building		V_{GS} =10V, I_D =3A			90	mΩ
Drain to Source On-state Resistance	R _{DS(ON)}	V_{GS} =4.5V, I_{D} =2A			120	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			490	780	pF
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V, f =1.0MHz		55		pF
Reverse Transfer Capacitance	C_{RSS}			40		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time (Note)	t _{D(ON)}			6		ns
Turn-ON Rise Time	t_{R}	V _{GS} =10V, V _{DS} =30V, I _D =1A,		5	42	ns
Turn-OFF Delay Time	t _{D(OFF)}	$R_D = 30\Omega$, $R_G = 3.3\Omega$		16		ns
Turn-OFF Fall-Time	t _F			3	58	ns
Total Gate Charge (Note)	Q_G			6	10	nC
Gate Source Charge	Q_GS	$V_{GS} = 4.5 \text{V}, V_{DS} = 48 \text{V}, I_D = 3 \text{A}$		1.6		nC
Gate Drain Charge	Q_GD			3		nC
SOURCE- DRAIN DIODE RATINGS AND CHA	ARACTERI	STICS				
Drain-Source Diode Forward Voltage (Note)	V_{SD}	I _S =1.2A, V _{GS} =0V			1.2	V
Reverse Recovery Time	t _{rr}	1 -24)/ -0)/ 41/44-4024/:-		25		ns
Reverse Recovery Charge	Q_{RR}	I_S =3A, V_{GS} =0V, dI/dt=100A/ μ s		26		nC
Note: Dulas width < 200us, duty avalo < 20/						

Note: Pulse width ≤300µs, duty cycle≤2%.

■ TEST WAVEFORMS



Switching Time Waveform



Gate Charge Waveform

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